

RJL5013DPP

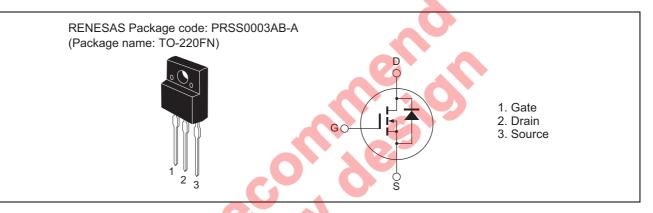
Silicon N Channel MOS FET High Speed Power Switching

> REJ03G1754-0100 Rev.1.00 Nov 17, 2008

Features

- Built-in fast recovery diode
- Low on-resistance
- Low leakage current
- High speed switching

Outline



Absolute Maximum Ratings

			$(Ta = 25^{\circ}C)$
Item 💊 🚺	Symbol	Ratings	Unit
Drain to source voltage	V _{DSS}	500	V
Gate to source voltage	V _{GSS}	±30	V
Drain current	ID ^{Note4}	14	А
Drain peak current	Note1 D (pulse)	42	А
Body-drain diode reverse drain current	I _{DR}	14	А
Body-drain diode reverse drain peak current	Note1 DR (pulse)	42	А
Avalanche current	I _{AP} ^{Note3}	3	А
Avalanche energy	E _{AR} ^{Note3}	0.5	mJ
Channel dissipation	Pch Note2	30	W
Channel to case thermal impedance	θch-c	4.17	°C/W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	–55 to +150	°C

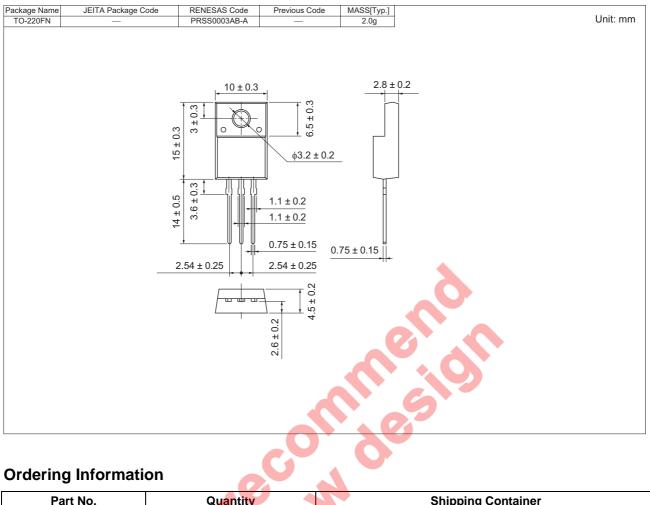
Notes: 1. $PW \le 10 \ \mu s$, duty cycle $\le 1\%$

- 2. Value at Tc = 25° C
- 3. STch = 25° C, Tch $\leq 150^{\circ}$ C
- 4. Limited by maximum safe operation area

Electrical Characteristics

Item Drain to source breakdown voltage Zero gate voltage drain current						$(Ta = 25^{\circ}C)$
Zero gate voltage drain current	Symbol	Min	Тур	Max	Unit	Test conditions
0 0	V _{(BR)DSS}	500	—	—	V	$I_{D} = 10 \text{ mA}, V_{GS} = 0$
	I _{DSS}	_	—	10	μΑ	$V_{DS} = 500 \text{ V}, V_{GS} = 0$
Gate to source leak current	I _{GSS}	_	_	±0.1	μΑ	V_{GS} = ±30 V, V_{DS} = 0
Gate to source cutoff voltage	V _{GS(off)}	2.0	_	4.0	V	$V_{DS} = 10 \text{ V}, \text{ I}_{D} = 1 \text{ mA}$
Static drain to source on state resistance	R _{DS(on)}	—	0.42	0.51	Ω	$I_D = 7 \text{ A}, V_{GS} = 10 \text{ V}^{Note5}$
Input capacitance	Ciss		1400		pF	V _{DS} = 25 V
Output capacitance	Coss		150		pF	$V_{GS} = 0$
Reverse transfer capacitance	Crss	_	19		рF	f = 1 MHz
Turn-on delay time	t _{d(on)}	_	30		ns	I _D = 7 A
Rise time	tr	_	24	—	ns	V _{GS} = 10 V
Turn-off delay time	t _{d(off)}	_	88	—	ns	R _L = 35.7 Ω
Fall time	t _f		17	—	ns	Rg = 10 Ω
Total gate charge	Qg	_	37.6	—	nC	V _{DD} = 400 V
Gate to source charge	Qgs	_	7.2	_	nC	V _{GS} = 10 V
Gate to drain charge	Qgd		17	-	nC	I _D = 14 A
Body-drain diode forward voltage	V _{DF}		0.95	1.60	V	I _F = 14 A, V _{GS} = 0 ^{Note5}
Body-drain diode reverse recovery time	t _{rr}	_	150		ns	I _F = 14 A, V _{GS} = 0 di _F /dt = 100 A/μs
Body-drain diode forward voltage Body-drain diode reverse recovery time Notes: 5. Pulse test	60	0	6	05		

Package Dimensions



Part No.	Quantity	Shipping Container
RJL5013DPP-00-T2	1050 pcs	Box (Tube)

2.0

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